

## ABSTRACT

An object of the present disclosure is to provide a reflective photomask blank and a reflective photomask  
5 having high transferability (particularly resolution) by making the most use of a phase shift effect. A reflective photomask blank (100) according to an aspect of the present disclosure includes a substrate (11), a reflective layer (12) having a multi-layer film  
10 structure, formed on the substrate (11), and configured to reflect an EUV light, a protective layer (13) formed on the reflective layer (12) and configured to protect the reflective layer (12), and an absorption layer (14) formed on the protective layer (13) and configured to  
15 absorb the EUV light, in which the absorption layer (14) has a phase difference in a range of 200 degrees or more and 280 degrees or less.

FIG. 1